

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) A complementary MISFET comprising:

a first linear body including an N-type MISFET; ~~and~~  
a second linear body including a P-type MISFET; and  
a separation region arranged between said first linear body and said second linear body,

wherein each cross section having plural regions for forming said MISFET is continuously or intermittently formed in the longitudinal direction.

2. (cancelled)

3. (currently amended) The complementary MISFET of claim 1, wherein at least one of said linear bodies ~~and/or~~ and said separation region is ~~are~~ formed of a material made of an organic semiconductor or electroconductive polymer.

4. (withdrawn) An integrated circuit comprising the complementary MISFET of claim 1.

5-6. (canceled)

7. (withdrawn) An integrated circuit comprising:

a plurality of linear bodies, each having a cross section which has a plurality of regions for forming a circuit element formed in said linear body and which is continuously or intermittently formed in the longitudinal direction.

8. (withdrawn) The integrated circuit of claim 7, wherein said integrated circuit is a semiconductor memory, an image sensor, or a PLA.

9. (withdrawn) The integrated circuit of claim 7, wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.

10. (withdrawn) The integrated circuit of claim 4, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.

11. (withdrawn - currently amended) The complementary MISFET of claim ~~2~~ 1, wherein said linear bodies and/or said separation region are formed of a material made of an organic semiconductor or electroconductive polymer.

12. (withdrawn - currently amended) An integrated circuit comprising the complementary MISFET of claim-~~2~~1.

13. (withdrawn) An integrated circuit comprising the complementary MISFET of claim 3.

14-17. (canceled)

18. (withdrawn) The integrated circuit of claim 8, wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.

19. (withdrawn) The integrated circuit of claim 7, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.

20. (withdrawn) The integrated circuit of claim 8, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.

21. (new) The complementary MISFET of claim 3, wherein the separation region is constituted from an insulating material formed between the plural linear bodies.

22. (new) The complementary MISFET of claim 21, wherein the insulating material is formed between the plural linear bodies by coating or vapor depositing.

23. (new) The complementary MISFET of claim 3, wherein the insulating material is constituted from an insulating film formed on a surface of the linear body.